



# 1N5817WS~1N5819WS

## Schottky Barrier Diodes

### Features

- High surge capability
- Low forward voltage drop
- Guarding for overvoltage protection
- Metal silicon junction, majority carrier conduction

SOD-323



1.Cathode —  — 2.Anode

### Marking Code:

1N5817WS: SJ

1N5818WS: SK

1N5819WS: SL

### Maximum Ratings and Electrical Characteristics

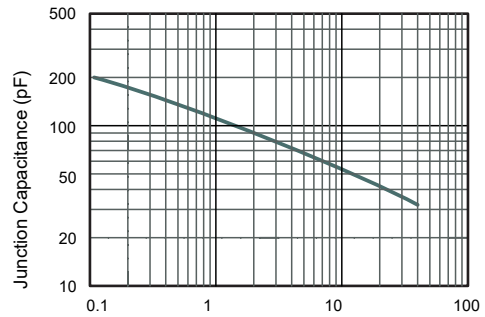
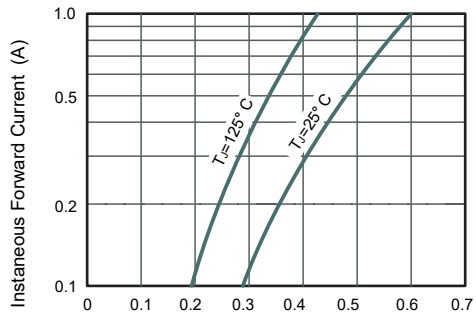
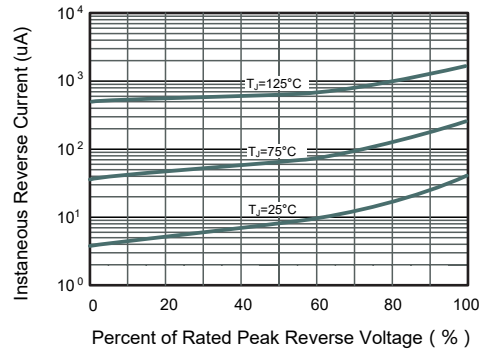
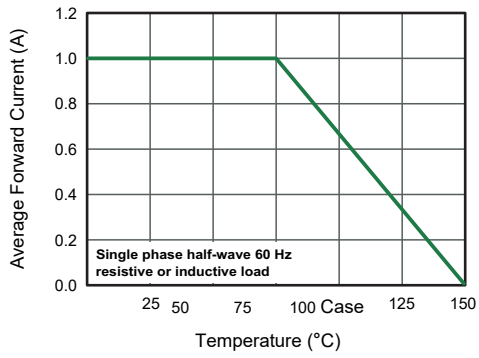
Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbols	1N5817WS	1N5818WS	1N5819WS	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	20	30	40	V
Maximum RMS Voltage	$V_{RMS}$	14	21	28	V
Maximum DC Blocking Voltage	$V_{DC}$	20	30	40	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	1.0			A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC method)	$I_{FSM}$	9			A
Maximum Instantaneous Forward Voltage					
at 1 A	$V_F$	0.45	0.55	0.6	V
at 3 A		0.75	0.875	0.9	
Maximum DC Reverse Current at Rated DC Blocking Voltage					
at $T_A = 25^\circ\text{C}$	$I_R$	1			mA
at $T_A = 100^\circ\text{C}$		10			
Typical Junction Capacitance	$C_j$	110			pF
Operating Junction Temperature	$T_J$	150			°C
Storage Temperature Range	$T_{STG}$	-55 to +150			°C



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## Typical Characteristic Curves





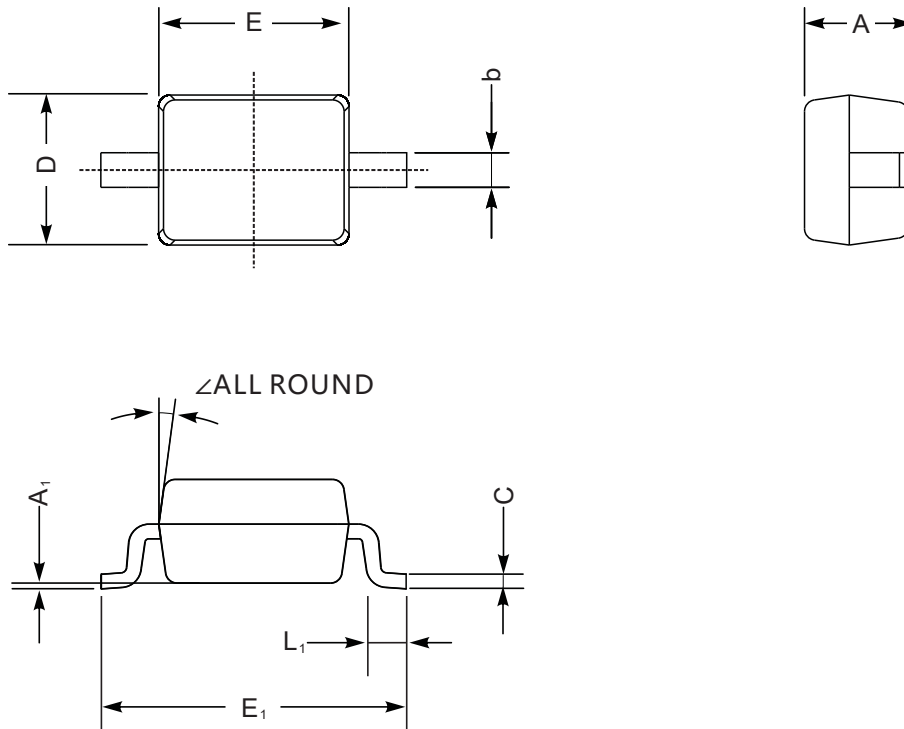
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### Package Outline

SOD-323

Dimensions in mm



UNIT		A	C	D	E	E <sub>1</sub>	b	L <sub>1</sub>	A <sub>1</sub>	∠
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2	9°
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—	
mil	max	43	5.9	55	70	108	16	16	8	
	min	32	3.1	47	63	100	9.8	7.9	—	